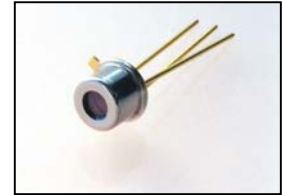




# PT511-2



## TECHNICAL DATA

### TO-Can PIN Photodiode

PT511-2 is an InGaAs pin structure based photodiode on InP by MOCVD method and planar diffusing technology. The sensitive area is  $\varnothing 300\mu\text{m}$  respectively. TO-46 package with flat glass lens.



#### Absolute Maximum Ratings

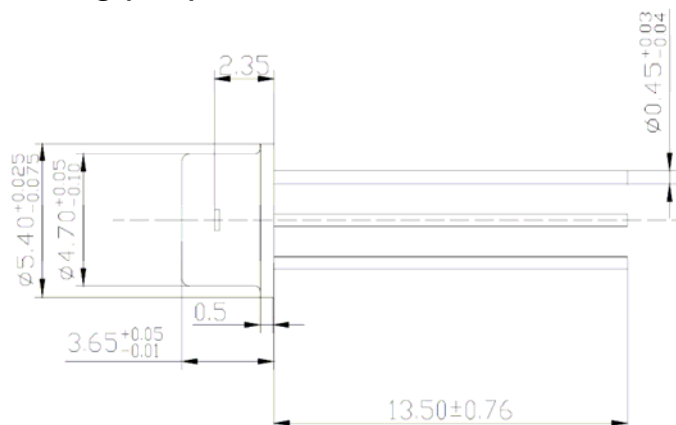
Item	Symbol	Value	Unit
Reverse Voltage	$U_R$	30	V
Reverse current	$I_R$	1000	$\mu\text{A}$
Forward current	$I_F$	5	mA
Power Dissipation	$P_D$	100	mW
Operating Temperature	$T_{opr}$	-40 ... +85	$^{\circ}\text{C}$
Storage Temperature	$T_{stg}$	-40 ... +125	$^{\circ}\text{C}$
Soldering Temperature *	$T_{sol}$	260	$^{\circ}\text{C}$

\* must be completed within 10 seconds

#### Specifications

Item	Value	Unit	
Wavelength Range	850 .. 1650	nm	
Sensitive Area	$\varnothing 300$	$\mu\text{m}$	
Unsaturated Power	10	dBm	
Responsivity	$\lambda=1300 \text{ nm}$	0.85	A/W
Capacitance (-5 V)	2	pF	
Dark Current (-5 V)	$\leq 1$	nA	
Rise/Fall time	3	ns	
Saturation Power	$> 10$	dB	

#### Drawing (mm)



#### Bottom View

